

## Amendments to the Claims

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Claims 1-27(cancelled).

Claim 28 (new) An integrated circuit structure, comprising:

at least two metal interconnect lines;

a liner comprising silicon and carbon located on and between said metal interconnect lines; and

a dielectric layer positioned between said metal interconnect lines, the liner positioned between at least a portion of the dielectric layer and the metal interconnect lines.

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Claim 29 (new): The integrated circuit structure of Claim 28, wherein the liner is selected from the group consisting of silicon carbide, silicon oxy-carbide, and silicon boron-carbide.

Claim 30 (new): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises an intralevel dielectric layer positioned between metal interconnect lines in a level of the integrated circuit structure.

Claim 31 (new): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises an interlevel dielectric layer positioned between conductive elements in different levels of the integrated circuit structure.

Claim 32 (new): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises a fluorinated dielectric material.

Claim 33 (new): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises polytetrafluoroethylene (PTFE).

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